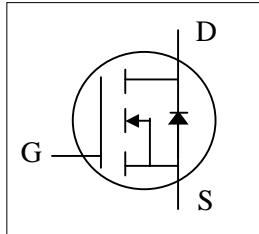
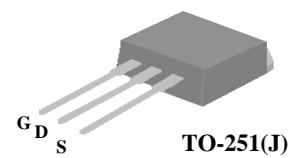


- ▼ Low Gate Charge
- ▼ Simple Drive Requirement
- ▼ Fast Switching Characteristic
- ▼ RoHS Compliant & Halogen-Free



BV_{DSS}	60V
$R_{DS(ON)}$	12mΩ
I_D	68A



Description

XP9974A series are innovated design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications. The straight lead version TO-251 package is widely preferred for all commercial-industrial through hole applications.

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_C = 25^\circ C$	Drain Current, $V_{GS} @ 10V$	68	A
$I_D @ T_C = 100^\circ C$	Drain Current, $V_{GS} @ 10V$	43	A
I_{DM}	Pulsed Drain Current ¹	272	A
$P_D @ T_C = 25^\circ C$	Total Power Dissipation	104	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Value	Units
R_{thj-c}	Maximum Thermal Resistance, Junction-case	1.2	°C/W
R_{thj-a}	Maximum Thermal Resistance, Junction-ambient	110	°C/W

Electrical Characteristics@ $T_j=25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	60	-	-	V
$R_{\text{DS(ON)}}$	Static Drain-Source On-Resistance ²	$V_{\text{GS}}=10\text{V}, I_{\text{D}}=45\text{A}$	-	-	12	$\text{m}\Omega$
		$V_{\text{GS}}=4.5\text{V}, I_{\text{D}}=30\text{A}$	-	-	15	$\text{m}\Omega$
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$	1	-	3	V
g_{fs}	Forward Transconductance	$V_{\text{DS}}=10\text{V}, I_{\text{D}}=30\text{A}$	-	71	-	S
I_{DSS}	Drain-Source Leakage Current	$V_{\text{DS}}=60\text{V}, V_{\text{GS}}=0\text{V}$	-	-	25	μA
I_{GSS}	Gate-Source Leakage	$V_{\text{GS}}=\pm 20\text{V}, V_{\text{DS}}=0\text{V}$	-	-	± 100	nA
Q_{g}	Total Gate Charge	$I_{\text{D}}=30\text{A}$	-	33	53	nC
Q_{gs}	Gate-Source Charge		-	5	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge		-	21	-	nC
$t_{\text{d(on)}}$	Turn-on Delay Time	$V_{\text{DS}}=30\text{V}$	-	10	-	ns
t_{r}	Rise Time		-	43	-	ns
$t_{\text{d(off)}}$	Turn-off Delay Time		-	47	-	ns
t_{f}	Fall Time	$V_{\text{GS}}=10\text{V}$	-	80	-	ns
C_{iss}	Input Capacitance		-	2680	4280	pF
C_{oss}	Output Capacitance		-	260	-	pF
C_{rss}	Reverse Transfer Capacitance	$f=1.0\text{MHz}$	-	180	-	pF
R_{g}	Gate Resistance		-	1.9	3.8	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage ²	$I_{\text{S}}=45\text{A}, V_{\text{GS}}=0\text{V}$	-	-	1.3	V
t_{rr}	Reverse Recovery Time	$I_{\text{S}}=10\text{A}, V_{\text{GS}}=0\text{V},$ $dI/dt=100\text{A}/\mu\text{s}$	-	30	-	ns
Q_{rr}	Reverse Recovery Charge		-	18	-	nC

Notes:

1.Pulse width limited by Max. junction temperature.

2.Pulse test

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

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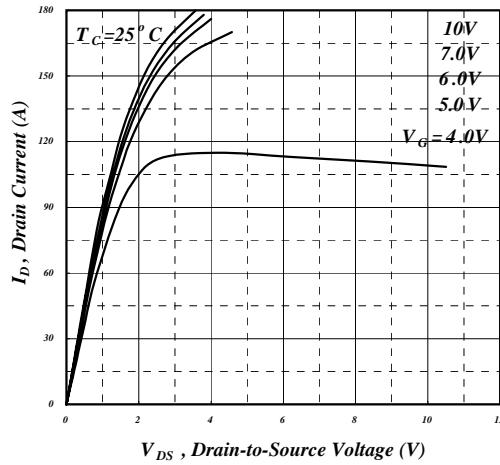


Fig 1. Typical Output Characteristics

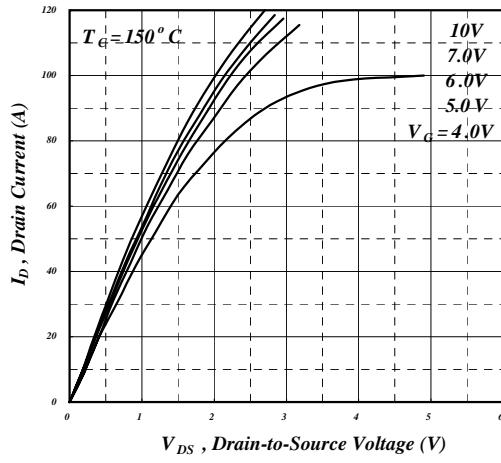


Fig 2. Typical Output Characteristics

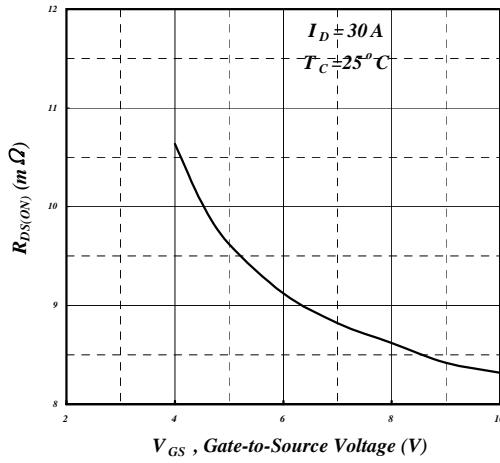


Fig 3. On-Resistance v.s. Gate Voltage

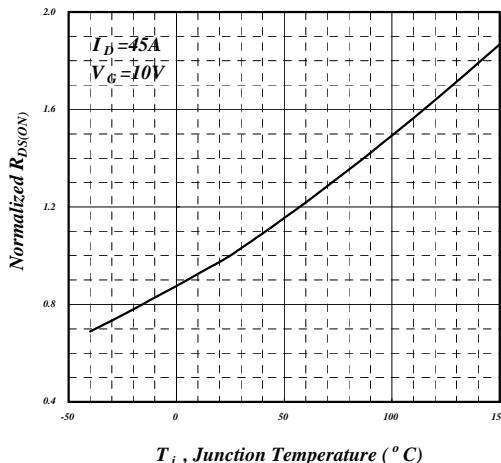


Fig 4. Normalized On-Resistance v.s. Junction Temperature

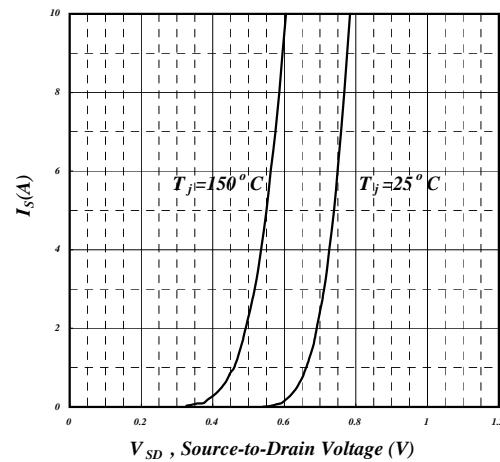


Fig 5. Forward Characteristic of Reverse Diode

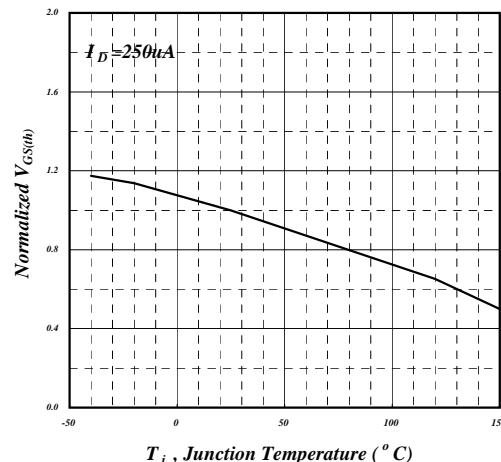


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

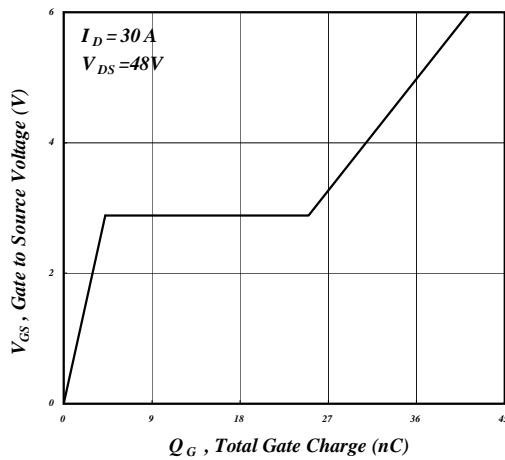


Fig 7. Gate Charge Characteristics

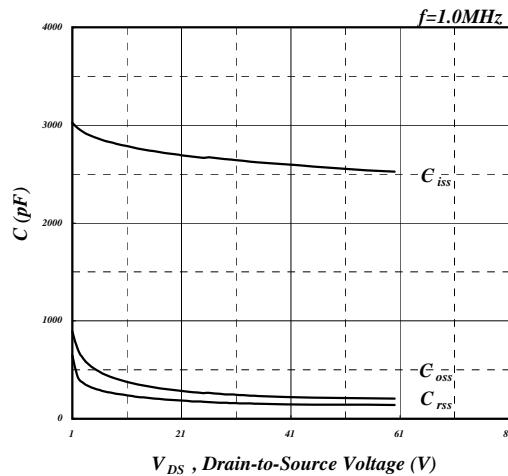


Fig 8. Typical Capacitance Characteristics

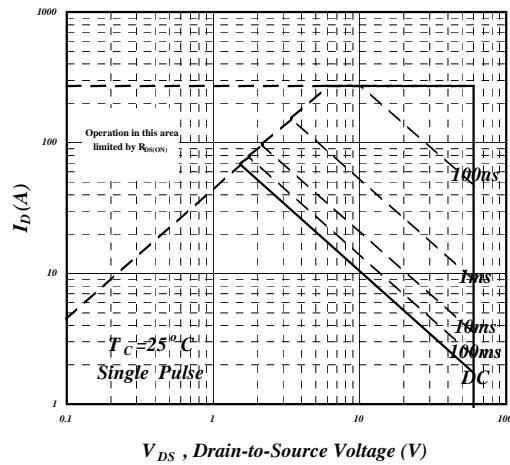


Fig 9. Maximum Safe Operating Area

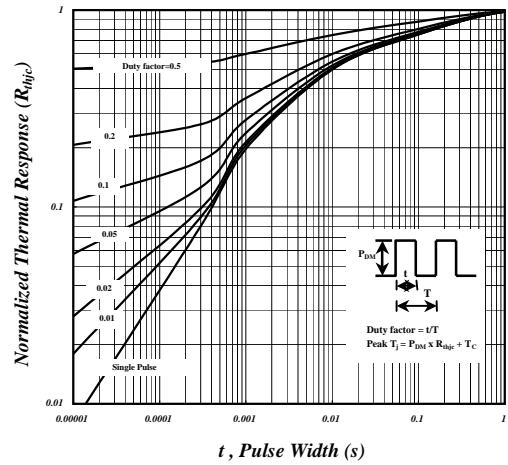


Fig 10. Effective Transient Thermal Impedance

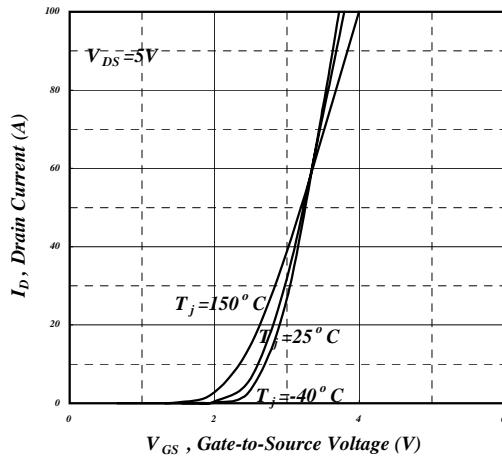


Fig 11. Transfer Characteristics

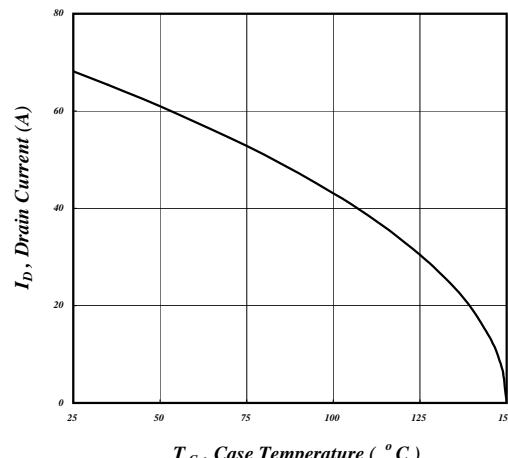
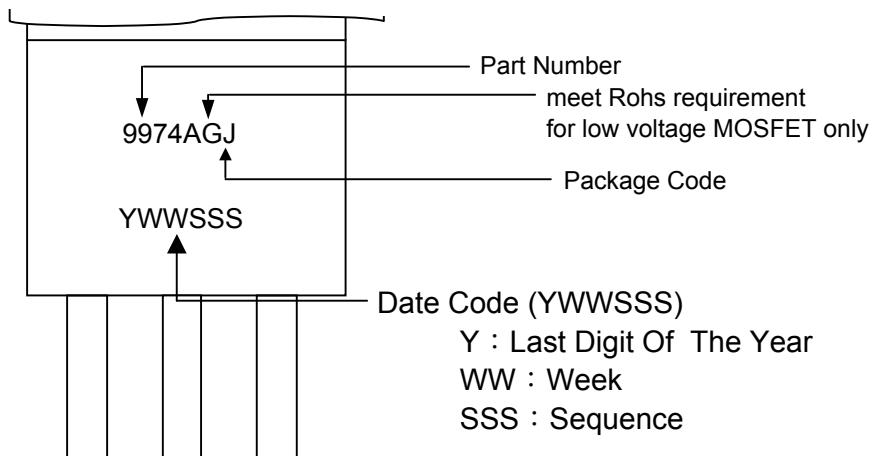
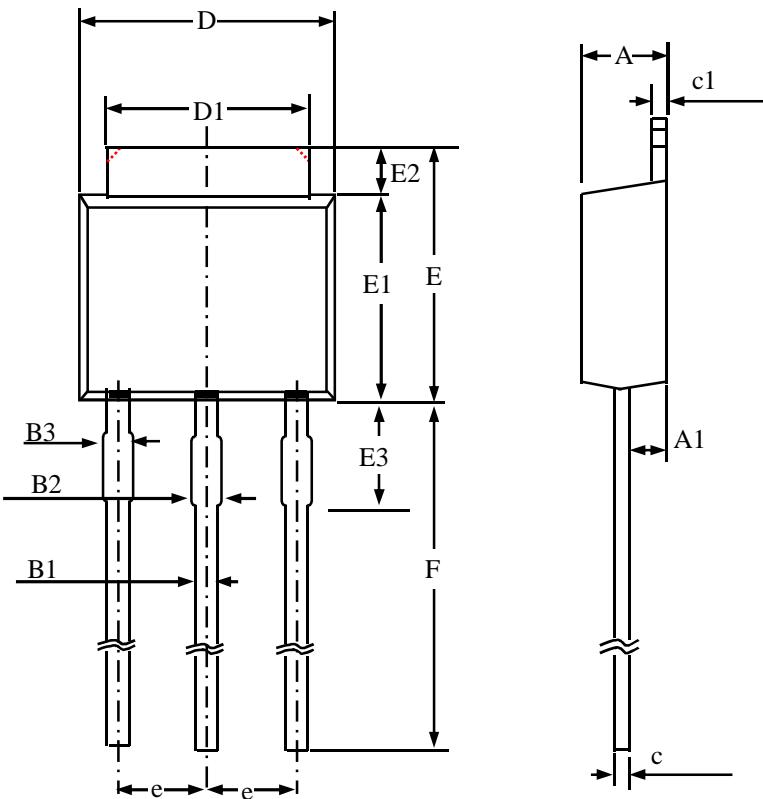


Fig 12. Drain Current v.s. Case Temperature

MARKING INFORMATION

Package Outline : TO-251



SYMBOLS	Millimeters		
	MIN	NOM	MAX
A	2.10	2.30	2.50
A1	0.80	1.15	1.50
B1	0.40	0.70	1.00
B2	0.60	0.88	1.15
B3	0.50	0.83	1.15
c	0.30	0.50	0.70
c1	0.30	0.50	0.70
D	6.30	6.55	6.80
D1	4.80	5.20	5.60
E	6.70	7.10	7.50
E1	5.30	5.80	6.30
E2	0.50	1.10	1.70
E3	1.30	1.80	2.30
e	----	2.30	----
F	7.00	8.33	9.65

1. All Dimensions Are in Millimeters.

2. Dimension Does Not Include Mold Protrusions.

TO-251 FOOTPRINT :

